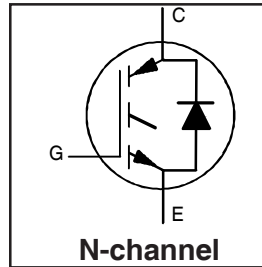


# IRG4BC20UD-SPbF

INSULATED GATE BIPOLAR TRANSISTOR WITH ULTRAFAST SOFT RECOVERY DIODE      UltraFast CoPack IGBT

## Features

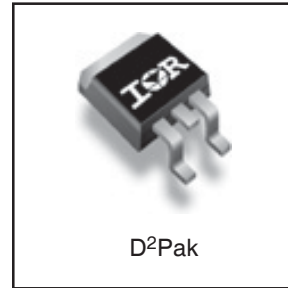
- UltraFast: Optimized for high operating frequencies 8-40 kHz in hard switching, >200kHz in resonant mode
- Generation 4 IGBT design provides tighter parameter distribution and higher efficiency than Generation 3
- IGBT co-packaged with HEXFRED™ ultrafast, ultra-soft-recovery anti-parallel diodes for use in bridge configurations
- Industry standard D<sup>2</sup>Pak package
- Lead-Free



$V_{CES} = 600V$
$V_{CE(on) typ.} = 1.85V$
@ $V_{GE} = 15V, I_C = 6.5A$

## Benefits

- Generation 4 IGBTs offers highest efficiencies available
- Optimized for specific application conditions
- HEXFRED diodes optimized for performance with IGBTs . Minimized recovery characteristics require less/no snubbing
- Designed to be a "drop-in" replacement for equivalent industry-standard Generation 3 IR IGBTs



## Absolute Maximum Ratings

	Parameter	Max.	Units
$V_{CES}$	Collector-to-Emitter Voltage	600	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	13	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	6.5	
$I_{CM}$	Pulsed Collector Current ①	52	
$I_{LM}$	Clamped Inductive Load Current ②	52	
$I_F @ T_C = 100^\circ C$	Diode Continuous Forward Current	7.0	
$I_{FM}$	Diode Maximum Forward Current	52	
$V_{GE}$	Gate-to-Emitter Voltage	$\pm 20$	V
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	60	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	24	
$T_J$	Operating Junction and	-55 to +150	°C
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	

## Thermal Resistance

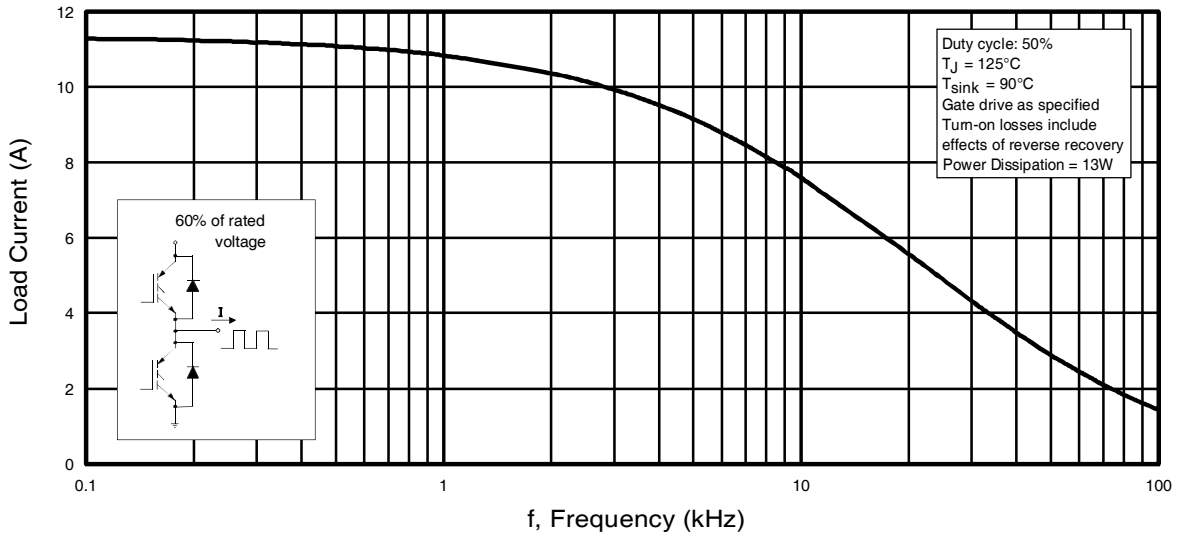
	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	2.1	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.5	—	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	—	40	
Wt	Weight	1.44	—	g (oz)

## Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)

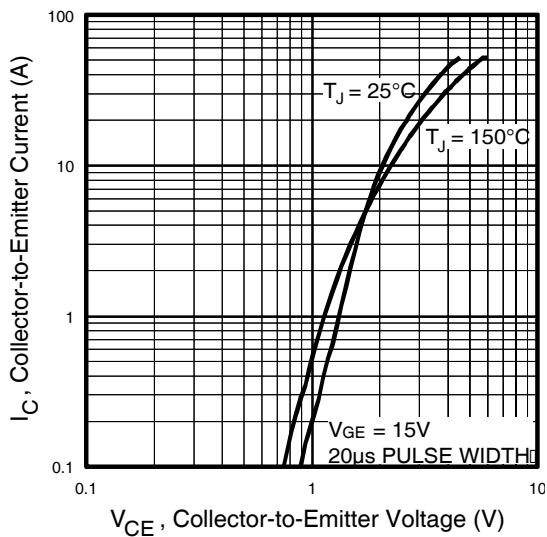
	Parameter	Min.	Typ.	Max.	Units	Conditions
V <sub>(BR)CES</sub>	Collector-to-Emitter Breakdown Voltage <sup>③</sup>	600	—	—	V	V <sub>GE</sub> = 0V, I <sub>C</sub> = 250μA
ΔV <sub>(BR)CES</sub> /ΔT <sub>J</sub>	Temperature Coeff. of Breakdown Voltage	—	0.69	—	V/°C	V <sub>GE</sub> = 0V, I <sub>C</sub> = 1.0mA
V <sub>CE(on)</sub>	Collector-to-Emitter Saturation Voltage	—	1.85	2.1	V	I <sub>C</sub> = 6.5A
		—	2.27	—		I <sub>C</sub> = 13A
		—	1.87	—		I <sub>C</sub> = 6.5A, T <sub>J</sub> = 150°C
V <sub>GE(th)</sub>	Gate Threshold Voltage	3.0	—	6.0		V <sub>CE</sub> = V <sub>GE</sub> , I <sub>C</sub> = 250μA
ΔV <sub>GE(th)</sub> /ΔT <sub>J</sub>	Temperature Coeff. of Threshold Voltage	—	-11	—	mV/°C	V <sub>CE</sub> = V <sub>GE</sub> , I <sub>C</sub> = 250μA
g <sub>fe</sub>	Forward Transconductance <sup>④</sup>	1.4	4.3	—	S	V <sub>CE</sub> = 100V, I <sub>C</sub> = 6.5A
I <sub>CES</sub>	Zero Gate Voltage Collector Current	—	—	250	μA	V <sub>GE</sub> = 0V, V <sub>CE</sub> = 600V
		—	—	1700		V <sub>GE</sub> = 0V, V <sub>CE</sub> = 600V, T <sub>J</sub> = 150°C
V <sub>FM</sub>	Diode Forward Voltage Drop	—	1.4	1.7	V	I <sub>C</sub> = 8.0A
		—	1.3	1.6		I <sub>C</sub> = 8.0A, T <sub>J</sub> = 150°C
I <sub>GES</sub>	Gate-to-Emitter Leakage Current	—	—	±100	nA	V <sub>GE</sub> = ±20V

## Switching Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)

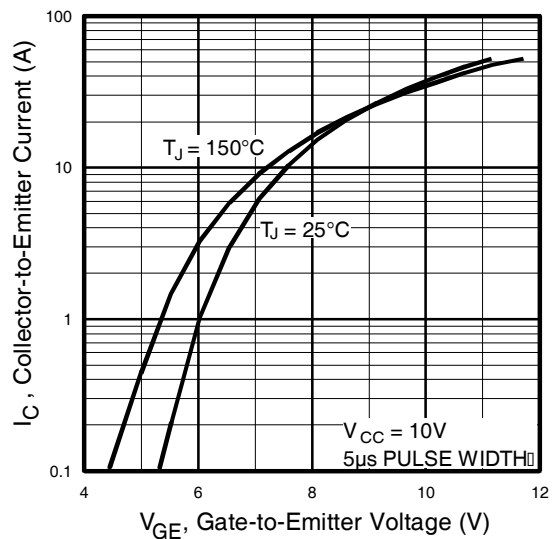
	Parameter	Min.	Typ.	Max.	Units	Conditions
Q <sub>g</sub>	Total Gate Charge (turn-on)	—	27	41	nC	I <sub>C</sub> = 6.5A
Q <sub>ge</sub>	Gate - Emitter Charge (turn-on)	—	4.5	6.8		V <sub>CC</sub> = 400V
Q <sub>gc</sub>	Gate - Collector Charge (turn-on)	—	10	16		V <sub>GE</sub> = 15V
t <sub>d(on)</sub>	Turn-On Delay Time	—	39	—	ns	T <sub>J</sub> = 25°C
t <sub>r</sub>	Rise Time	—	15	—		I <sub>C</sub> = 6.5A, V <sub>CC</sub> = 480V
t <sub>d(off)</sub>	Turn-Off Delay Time	—	93	140		V <sub>GE</sub> = 15V, R <sub>G</sub> = 50Ω
t <sub>f</sub>	Fall Time	—	110	170	mJ	Energy losses include "tail" and diode reverse recovery.
E <sub>on</sub>	Turn-On Switching Loss	—	0.16	—		See Fig. 9, 10, 11, 18
E <sub>off</sub>	Turn-Off Switching Loss	—	0.13	—		
E <sub>ts</sub>	Total Switching Loss	—	0.29	0.3	mJ	T <sub>J</sub> = 150°C, See Fig. 9, 10, 11, 18
t <sub>d(on)</sub>	Turn-On Delay Time	—	38	—		I <sub>C</sub> = 6.5A, V <sub>CC</sub> = 480V
t <sub>r</sub>	Rise Time	—	17	—		V <sub>GE</sub> = 15V, R <sub>G</sub> = 50Ω
t <sub>d(off)</sub>	Turn-Off Delay Time	—	100	—	mJ	Energy losses include "tail" and diode reverse recovery.
t <sub>f</sub>	Fall Time	—	220	—		
E <sub>ts</sub>	Total Switching Loss	—	0.49	—		
L <sub>E</sub>	Internal Emitter Inductance	—	7.5	—	nH	Measured 5mm from package
C <sub>ies</sub>	Input Capacitance	—	530	—	pF	V <sub>GE</sub> = 0V
C <sub>oes</sub>	Output Capacitance	—	39	—		V <sub>CC</sub> = 30V
C <sub>res</sub>	Reverse Transfer Capacitance	—	7.4	—		f = 1.0MHz
t <sub>rr</sub>	Diode Reverse Recovery Time	—	37	55	ns	T <sub>J</sub> = 25°C See Fig. 14
		—	55	90		T <sub>J</sub> = 125°C
I <sub>rr</sub>	Diode Peak Reverse Recovery Current	—	3.5	5.0	A	T <sub>J</sub> = 25°C See Fig. 15
		—	4.5	8.0		T <sub>J</sub> = 125°C
Q <sub>rr</sub>	Diode Reverse Recovery Charge	—	65	138	nC	T <sub>J</sub> = 25°C See Fig. 16
		—	124	360		T <sub>J</sub> = 125°C
di <sub>(rec)M</sub> /dt	Diode Peak Rate of Fall of Recovery During t <sub>b</sub>	—	240	—	A/μs	T <sub>J</sub> = 25°C See Fig. 17
		—	210	—		T <sub>J</sub> = 125°C



**Fig. 1** - Typical Load Current vs. Frequency  
 (Load Current =  $I_{\text{RMS}}$  of fundamental)

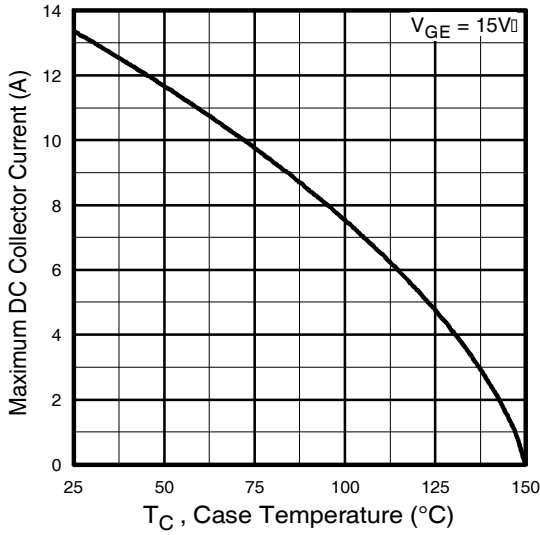


**Fig. 2** - Typical Output Characteristics

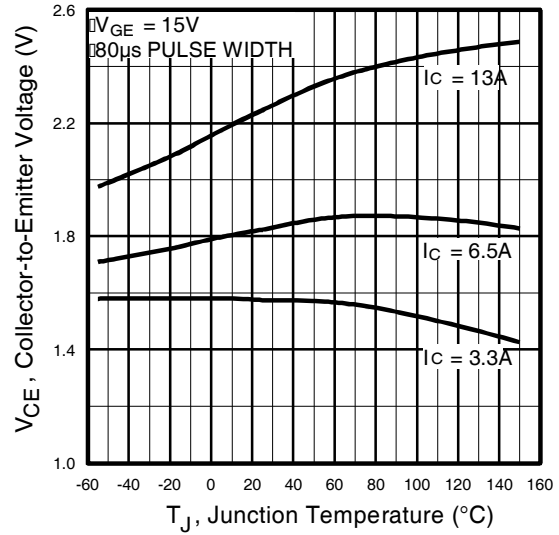


**Fig. 3** - Typical Transfer Characteristics

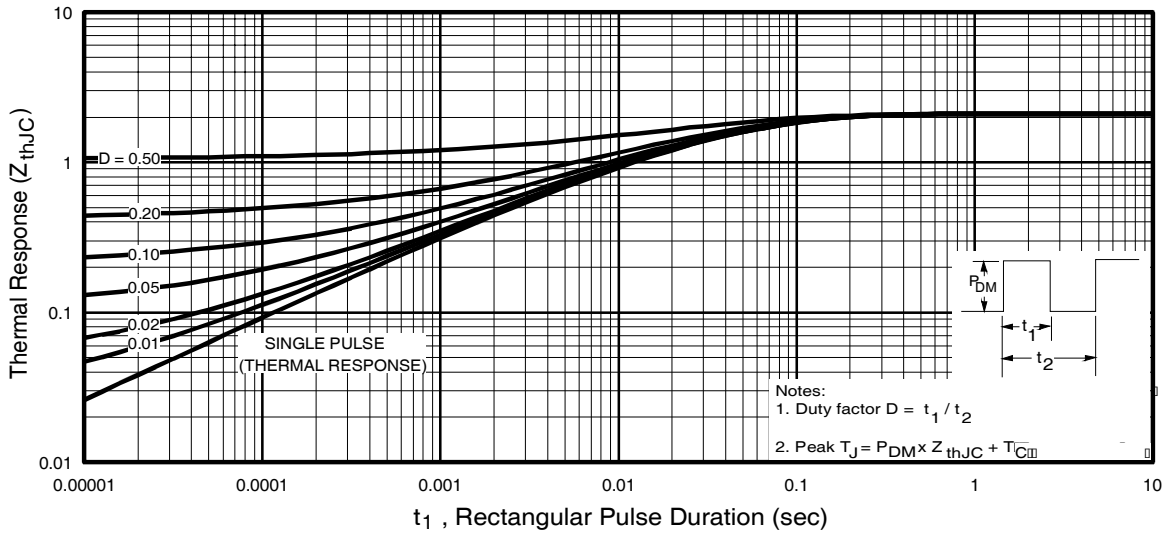
# IRG4BC20UD-SPbF



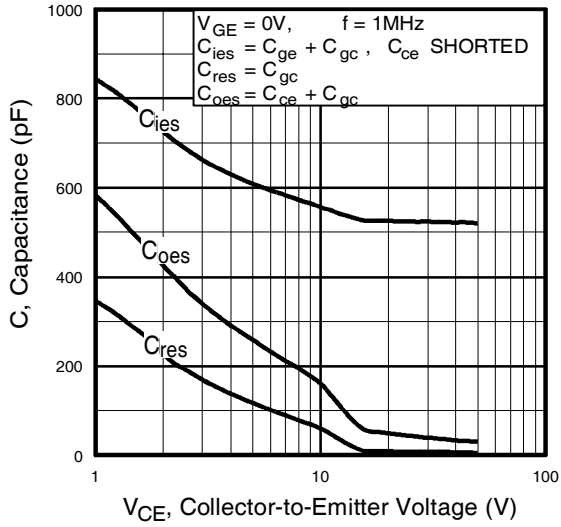
**Fig. 4** - Maximum Collector Current vs. Case Temperature



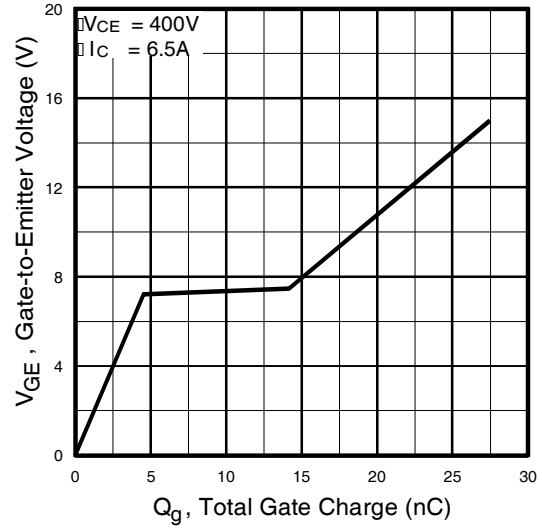
**Fig. 5** - Typical Collector-to-Emitter Voltage vs. Junction Temperature



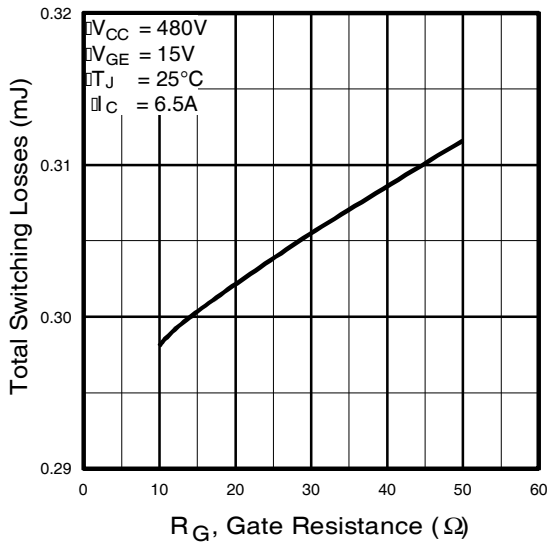
**Fig. 6** - Maximum IGBT Effective Transient Thermal Impedance, Junction-to-Case



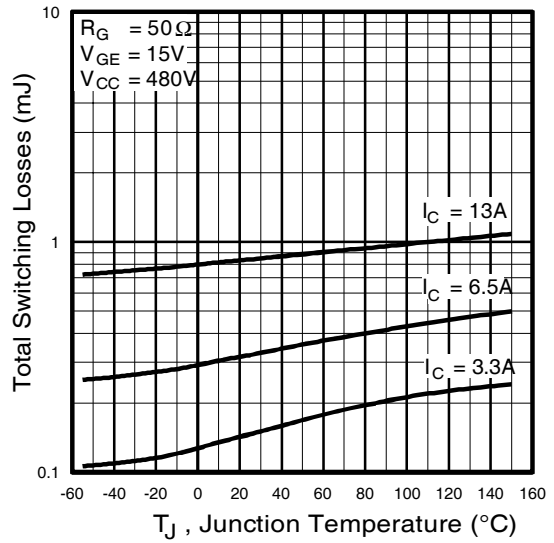
**Fig. 7** - Typical Capacitance vs. Collector-to-Emitter Voltage



**Fig. 8** - Typical Gate Charge vs. Gate-to-Emitter Voltage

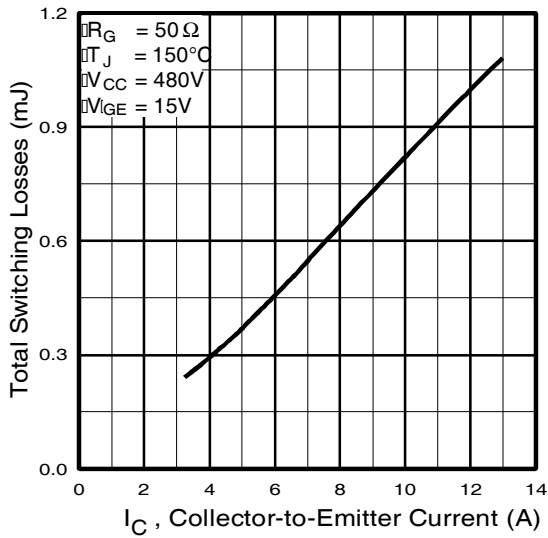


**Fig. 9** - Typical Switching Losses vs. Gate Resistance

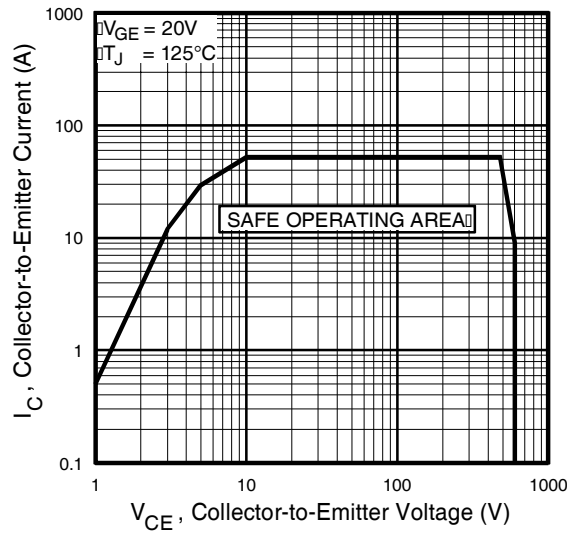


**Fig. 10** - Typical Switching Losses vs. Junction Temperature

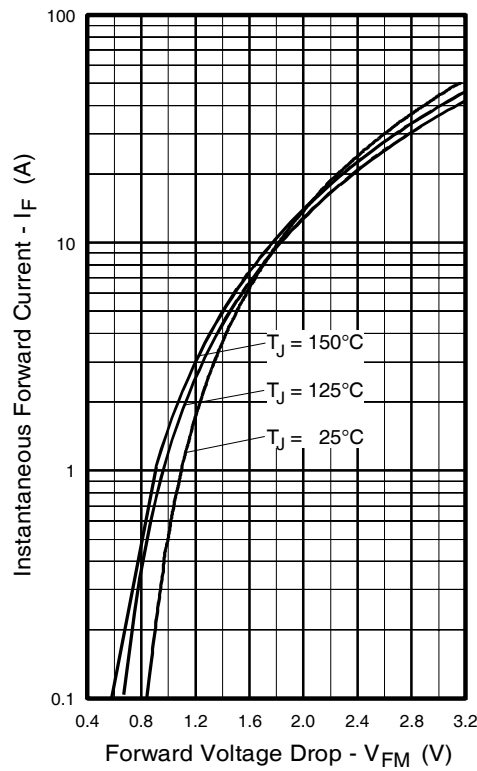
# IRG4BC20UD-SPbF



**Fig. 11** - Typical Switching Losses vs. Collector-to-Emitter Current



**Fig. 12** - Turn-Off SOA



**Fig. 13** - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

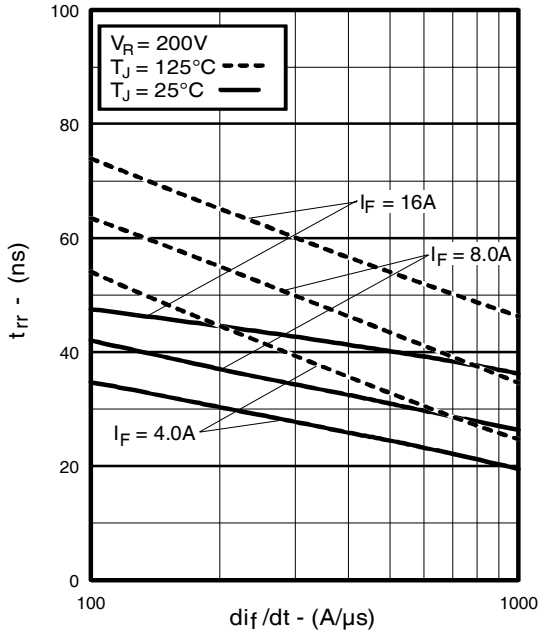


Fig. 14 - Typical Reverse Recovery vs.  $di_f/dt$

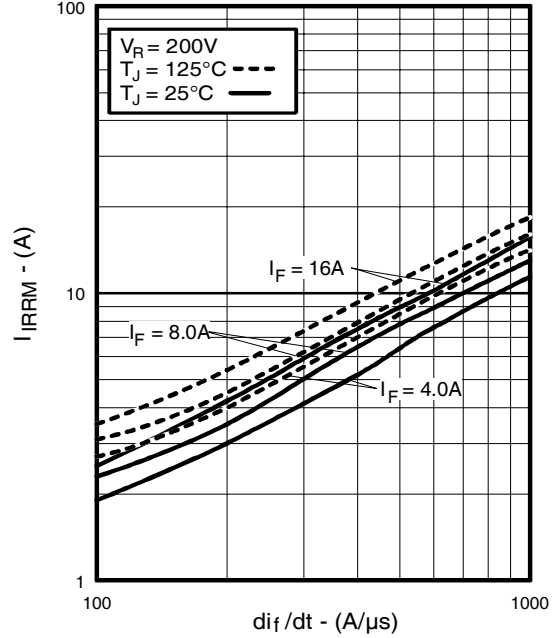


Fig. 15 - Typical Recovery Current vs.  $di_f/dt$

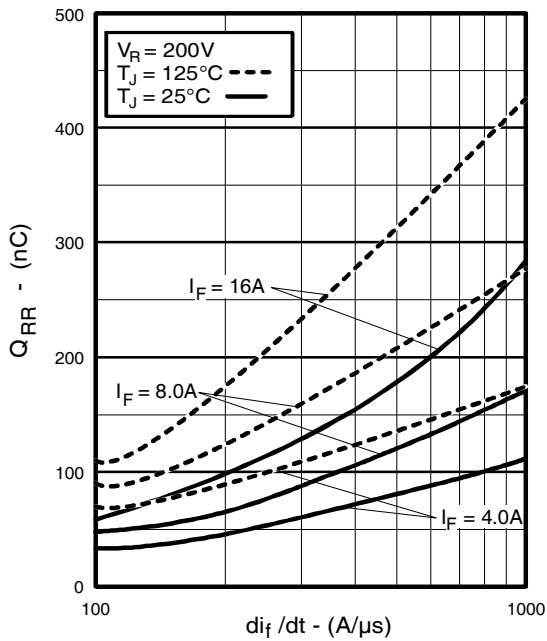


Fig. 16 - Typical Stored Charge vs.  $di_f/dt$

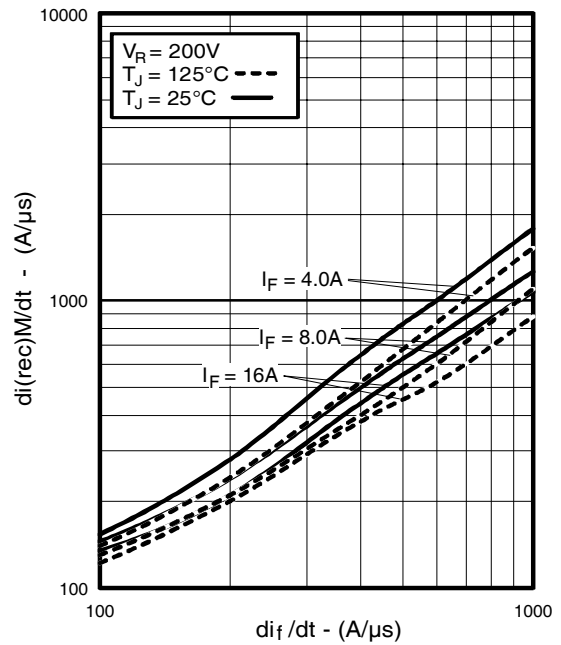
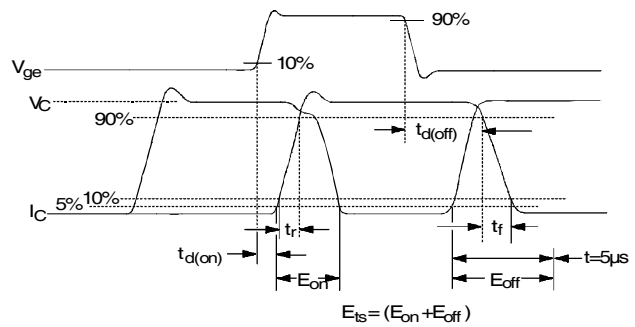


Fig. 17 - Typical  $di_{(rec)M}/dt$  vs.  $di_f/dt$

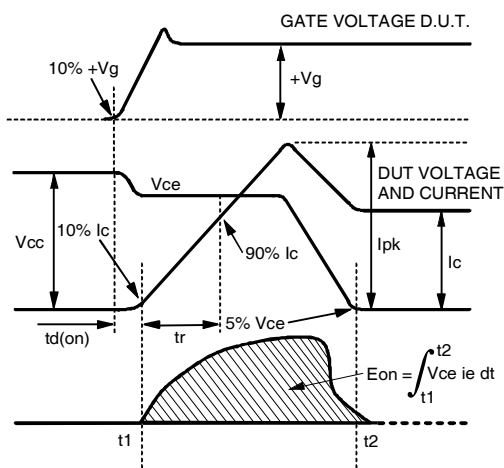
# IRG4BC20UD-SPbF



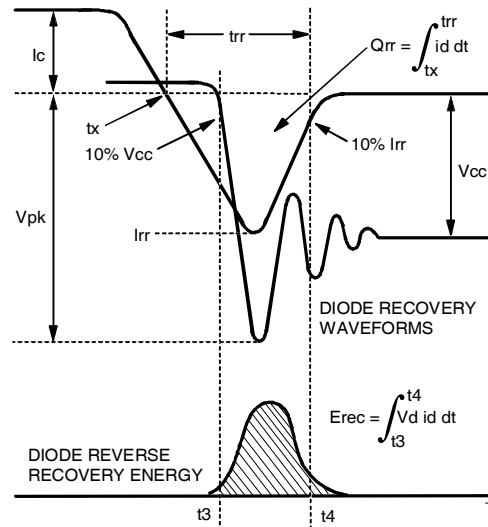
**Fig. 18a** - Test Circuit for Measurement of  $I_{LM}$ ,  $E_{on}$ ,  $E_{off}(\text{diode})$ ,  $t_{rr}$ ,  $Q_{rr}$ ,  $I_{rr}$ ,  $t_{d(on)}$ ,  $t_r$ ,  $t_{d(off)}$ ,  $t_f$



**Fig. 18b** - Test Waveforms for Circuit of Fig. 18a, Defining  $E_{off}$ ,  $t_{d(off)}$ ,  $t_f$



**Fig. 18c** - Test Waveforms for Circuit of Fig. 18a, Defining  $E_{on}$ ,  $t_{d(on)}$ ,  $t_r$



**Fig. 18d** - Test Waveforms for Circuit of Fig. 18a, Defining  $E_{rec}$ ,  $t_{rr}$ ,  $Q_{rr}$ ,  $I_{rr}$



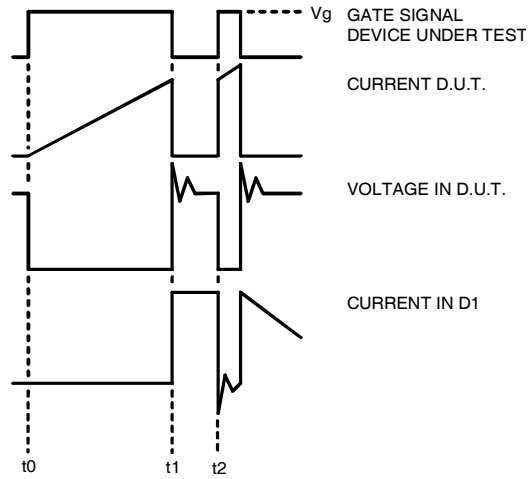


Figure 18e. Macro Waveforms for Figure 18a's Test Circuit

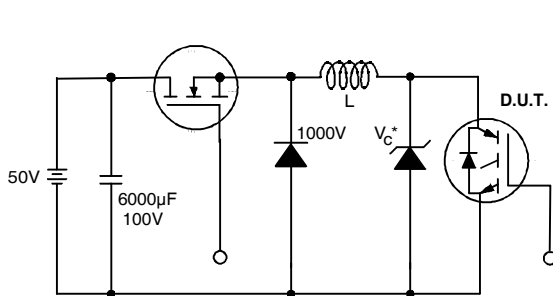
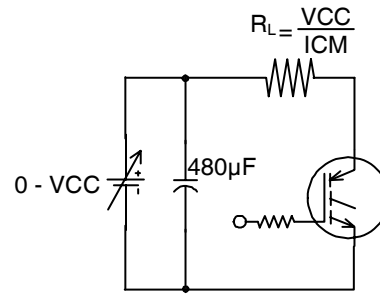


Figure 19. Clamped Inductive Load Test Circuit



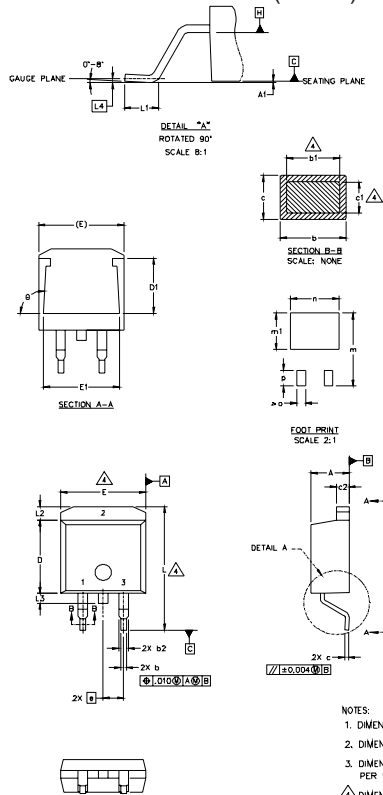
Pulsed Collector Current  
 Test Circuit

Figure 20. Pulsed Collector Current  
 Test Circuit

# IRG4BC20UD-SPbF

## D<sup>2</sup>Pak Package Outline

Dimensions are shown in millimeters (inches)



SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	
A1		0.127		.005	
b	0.51	0.99	.020	.039	4
b1	0.51	0.89	.020	.035	
b2	1.14	1.40	.045	.055	4
c	0.43	0.63	.017	.025	
c1	0.38	0.74	.015	.029	3
c2	1.14	1.40	.045	.055	
D	8.51	9.65	.335	.380	3
D1	5.33		.210		
E	9.65	10.67	.380	.420	3
E1	6.22		.245		
e	2.54	BSC	.100	BSC	
L	14.61	15.88	.575	.625	
L1	1.78	2.79	.070	.110	
L2		1.65		.065	
L3	1.27	1.78	.050	.070	
L4	0.25	BSC	.010	BSC	
m	17.78		.700		
m1	8.89		.350		
n	11.43		.450		
o	2.08		.082		
p	3.81		.150		
θ	90°	93°	90°	93°	

### LEAD ASSIGNMENTS

HEXFET	IGBTs, CoPACK	DIODES
1.- GATE	1.- GATE	1.- ANODE *
2.- DRAIN	2.- COLLECTOR	2.- CATHODE
3.- SOURCE	3.- EMITTER	3.- ANODE

\* PART DEPENDENT.

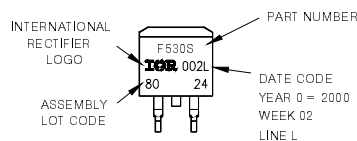
### NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES]
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [0.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
4. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
5. CONTROLLING DIMENSION: INCH.

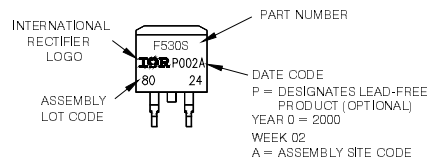
## D<sup>2</sup>Pak Part Marking Information

EXAMPLE: THIS IS AN IRF530S WITH  
LOT CODE 8024  
ASSEMBLED ON WW 02, 2000  
IN THE ASSEMBLY LINE 'L'

Note: 'P' in assembly line  
position indicates 'Lead-Free'



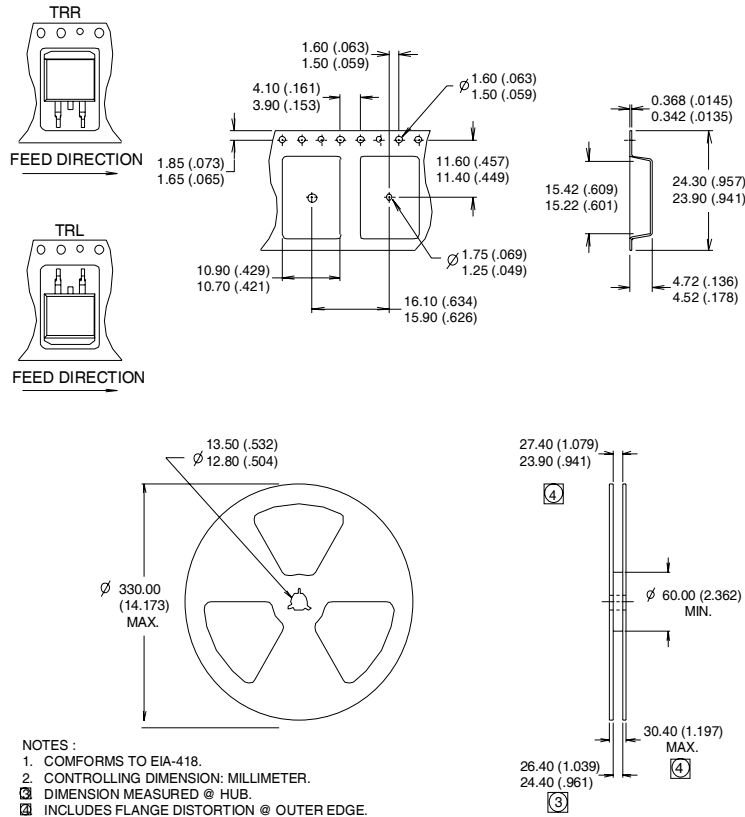
**OR**



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

## D<sup>2</sup>Pak Tape & Reel Information

Dimensions are shown in millimeters (inches)



### Notes:

- ① Repetitive rating:  $V_{GE}=20V$ ; pulse width limited by maximum junction temperature (Figure 20)
- ②  $V_{CC}=80\%(V_{CES})$ ,  $V_{GE}=20V$ ,  $L=10\mu H$ ,  $R_G = 50\Omega$  (Figure 19)
- ③ Pulse width  $\leq 80\mu s$ ; duty factor  $\leq 0.1\%$ .
- ④ Pulse width  $5.0\mu s$ , single shot.

Data and specifications subject to change without notice.  
This product has been designed and qualified for the Industrial market.  
Qualification Standards can be found on IR's Web site.

International  
IR Rectifier

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TAC Fax: (310) 252-7903

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